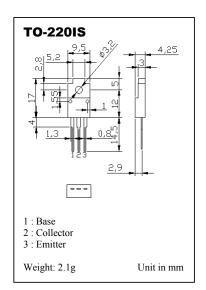
## NPN SILICON EPITAXIAL PLANAR TRANSISTOR

...designed for Audio, Series Regulator and General Purpose

...Complementary to PMB1626

## MAXIMUM RATINGS (T<sub>a</sub> = 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	Vсво	110	V
Collector Emitter Voltage	VCEO	110	V
Emitter Base Voltage	VEBO	5	V
Collector Current	lc	6	А
Base Current	Ів	1	А
Collector Dissipation Tc= 25 °C	Pc	30	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C



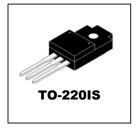
## ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector Cutoff Current	Ісво	Vcb=-110V	-	-	100	μA
Emitter Cutoff Current	IEBO	VEB=-5V	-	-	100	μA
Collector Emitter Breakdown Voltage	V(BR)CEO	Ic=-30mA	110	-	-	V
DC Current Gain	hfe	VCE=-4V, IC=-5A	5000	-	30000	-
Collector Emitter Saturation Voltage	VCE(sat)	Ic=-5A, I <sub>B</sub> =-5mA	-	-	2.5	V
Base Emitter Saturation Voltage	VBE(sat)	Ic=-5A, IB=-5mA	-	-	3	V
Transition Frequency	f⊤	Vce=-12V, Ie=-0.5A	-	100	-	MHz
Output Capacitance	Cob	V <sub>CB</sub> =-10V, f=1MHz	-	110	-	pF



## CLASSIFICATIONS OF hFE

Rank	0	Р	Y
Range	5000 to 12000	6500 to 20000	15000 to 30000



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